



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **HARADA, Akihiko et al.**

Serial No.: 09/717,143

Filed: November 22, 2000

Group Art Unit: 2826

Examiner: Ahmed Sefer

P.T.O. Confirmation No. 2927

#10/B  
1-303  
Payton

For: **INSULATED GATE TYPE SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME**

**RESPONSE UNDER 37 CFR §1.116**  
**- EXPEDITED RESPONSE -**  
**GROUP ART UNIT 2826**

**BOX AF**

Commissioner for Patents  
Washington, D.C. 20231

December 26, 2002

Sir:

In response to the Office Action dated **July 25, 2002**, please amend the above-identified application as follows:

**IN THE CLAIMS:**

Please ~~cancel~~ claim 4 without prejudice or disclaimer.

Please ~~amend~~ claims 1, 2, 3 and 5 as indicated below:

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DEC 30 2002  
TECHNOLOGY CENTER 2800

B1  
1. (Twice Amended) An insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, provided with a T-shaped gate electrode comprised of a trunk-shaped main gate electrode extending in parallel with respect to said semiconductor substrate, and a crosspiece-shaped conductor pattern extending in parallel with respect to said semiconductor substrate and also extending toward the width direction of said main gate electrode and having a